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View Online at https://aerobasegroup.com/nsn/5961-01-281-5577

Inclosure Material:
Ceramic or glass
Overall Length:
0.570 inches
Terminal Length:
Between 1.000 inches and 1.625 inches
Overall Diameter:
Between 0.215 inches and 0.235 inches
Function For Which Designed:
Transient suppressor
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
Do-13
Electrode Internally-electrically Connected To Case:
Cathode
Mounting Method:
Terminal
Features Provided:
Quality assurance level txv
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
15.2 breakdown voltage, dc and 16.8 breakdown voltage, dc
Current Rating Per Characteristic:
5.00 microamperes forward current, average peak
Power Rating Per Characteristic:
1.0 watts small-signal input power, common-collector major
Maximum Operating Tempurature Per Measurement Point:
175.0 degrees celsius ambient air
Precious Material And Location:
Terminal surfaces silver
Precious Material:
Silver
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
2 uninsulated wire lead
Specification Data:
81349-mil-s-19500/500 government specification

Shelf Life:

N/a

- Unit Of Measure:
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Demilitarization:

No

Fiig:

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